



TSM70N900CH C5G Information

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For Reference Only

Part Number TSM70N900CH C5G Manufacturer TSC America Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET, SINGLE, N-CHANNEL, SUPER**Package**TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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TSM70N900CH C5G Specifications

Manufacturer Part Number TSM70N900CH C5G Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 700V Current - Continuous Drain (Id) @ 25°C 4.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 9.7n C @ 10V Input Capacitance (Ciss) (Max) @ Vds 482pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 50W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
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PackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)700VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds482pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)50W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251 (IPAK)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 700V Current - Continuous Drain (Id) @ 25°C 4.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 9.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 482pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 50W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Toain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 4.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 9.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 482pF @ 100V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package TO-251 (IPAK) Package / Case	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)700VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds482pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)50W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251 (IPAK)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
Drain to Source Voltage (Vdss)700VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds482pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)50W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251 (IPAK)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case 4.5A (Tc) 4.5A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds482pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)50W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251 (IPAK)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	700V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	4.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 482pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 50W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	9.7nC @ 10V
FET Feature - Power Dissipation (Max) 50W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	482pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs900 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251 (IPAK)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	50W (Tc)
Mounting Type Through Hole Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	900 mOhm @ 1.5A, 10V
Supplier Device Package TO-251 (IPAK) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	TO-251 (IPAK)
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

TSM70N900CH C5G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM70N900CH C5G Payment Methods



















TSM70N900CH C5G Shipping Methods













If you have any question about TSM70N900CH C5G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com